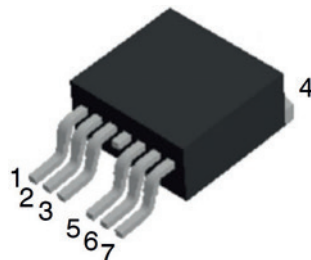
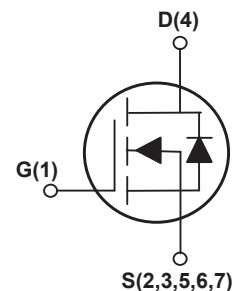


Main Product Characteristics

BV_{DSS}	100V
$R_{DS(ON)}$	1.7m Ω (Max.)
I_D	290A



TO-263-7L



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSGT71R710 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_C=25^{\circ}\text{C}$)	I_D	290	A
Drain Current-Continuous ($T_C=100^{\circ}\text{C}$)		188	
Drain Current-Pulsed ¹	I_{DM}	1160	A
Single Pulse Avalanche Energy ²	E_{AS}	2500	mJ
Single Pulse Avalanche Current ²	I_{AS}	100	A
Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_D	460	W
Power Dissipation-Derate above 25°C		3.06	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.33	$^{\circ}\text{C/W}$
Operating Junction Temperature Range	T_J	-55 To +175	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 To +175	$^{\circ}\text{C}$

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V, T _J =25°C	-	-	1	μA
		V _{DS} =100V, V _{GS} =0V, T _J =125°C	-	-	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	1.3	1.7	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250μA	2.1	-	3.9	V
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =15A	-	36	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3,4}	Q _g	V _{DS} =50V, I _D =20A, V _{GS} =10V	-	151	-	nC
Gate-Source Charge ^{3,4}	Q _{gs}		-	48	-	
Gate-Drain Charge ^{3,4}	Q _{gd}		-	30	-	
Turn-On Delay Time ^{3,4}	t _{d(on)}	V _{DD} =50V, R _G =6Ω, V _{GS} =10V, I _D =20A	-	36	-	nS
Rise Time ^{3,4}	t _r		-	26	-	
Turn-Off Delay Time ^{3,4}	t _{d(off)}		-	90	-	
Fall Time ^{3,4}	t _f		-	40	-	
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	10600	-	pF
Output Capacitance	C _{oss}		-	3742	-	
Reverse Transfer Capacitance	C _{rss}		-	61	-	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.2	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I _S	V _G =V _D =0V, Force Current	-	-	290	A
Pulsed Source Current	I _{SM}		-	-	580	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A, T _J =25°C	-	-	1.2	V
Reverse Recovery Time	t _{rr}	V _R =100V, I _S =20A, di/dt=500A/μs, T _J =25°C	-	55	-	nS
Reverse Recovery Charge	Q _{rr}		-	333	-	nC

Notes:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_G=25Ω, starting T_J=25°C.
3. Pulse test: pulse width ≤300us, duty cycle ≤2%.
4. Essentially independent of operation temperature.

Typical Electrical and Thermal Characteristic Curves

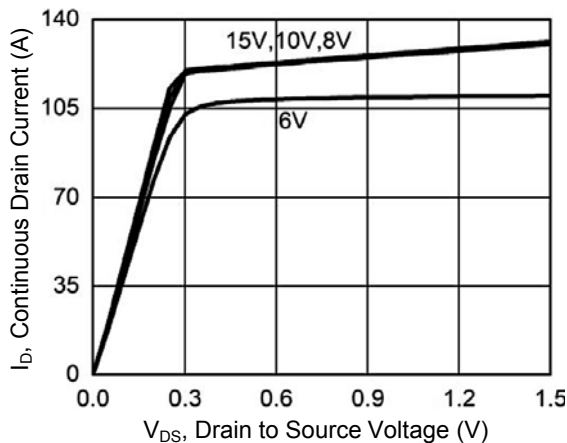


Figure 1. Typical Output Characteristics

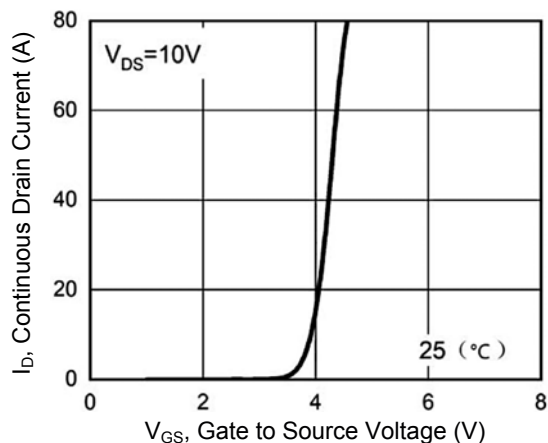


Figure 2. Typical Transfer Characteristics

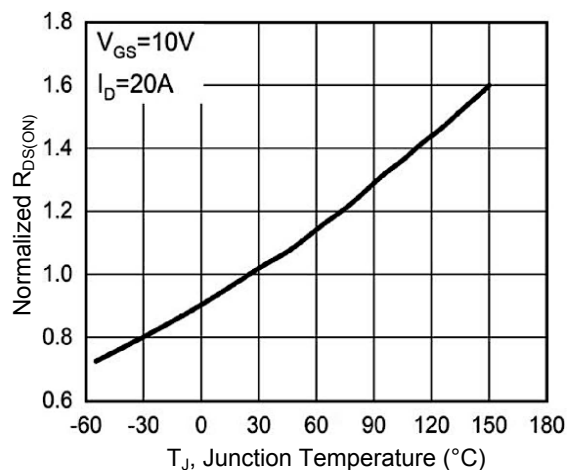


Figure 3. Normalized $R_{DS(ON)}$ vs. T_J

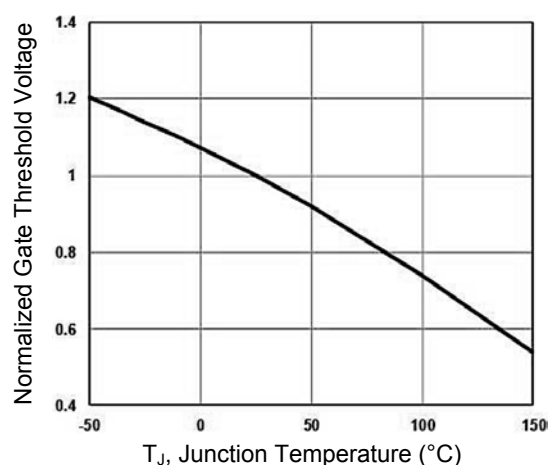


Figure 4. Normalized V_{th} vs. T_J

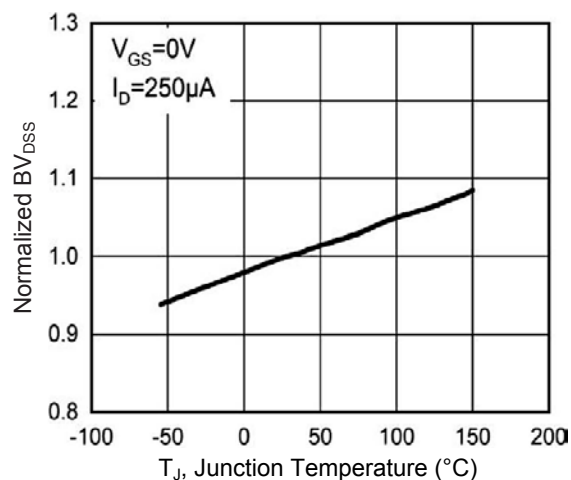


Figure 5. Normalized BV_{DS} vs. T_J

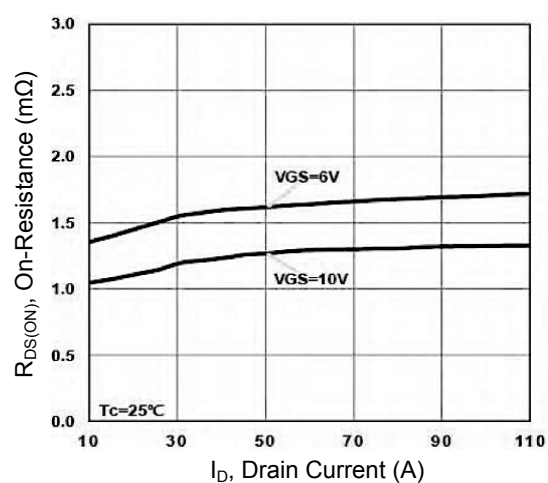


Figure 6. On-Resistance vs. I_D

Typical Electrical and Thermal Characteristic Curves

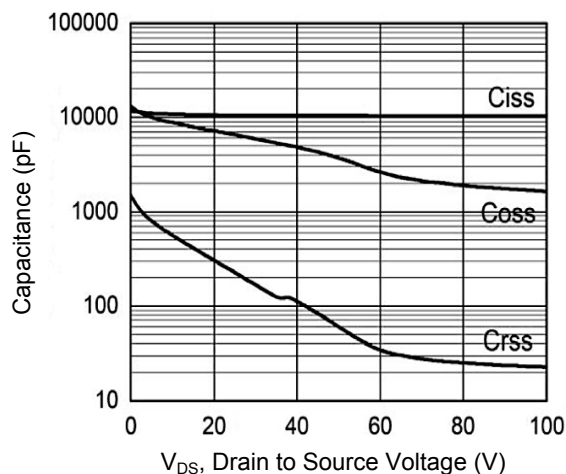


Figure 7. Capacitance Characteristics

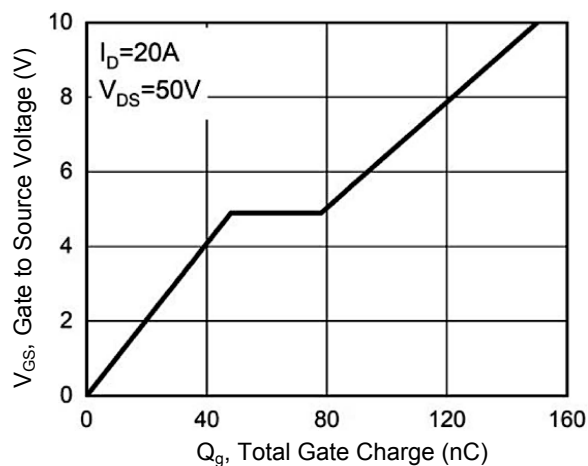


Figure 8. Gate Charge Characteristics

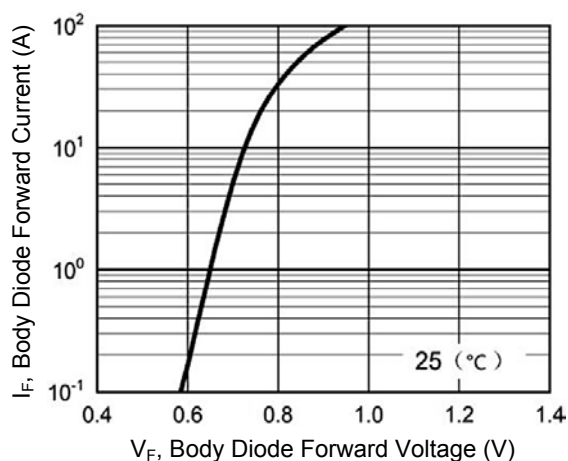


Figure 9. Body Diode Characteristics

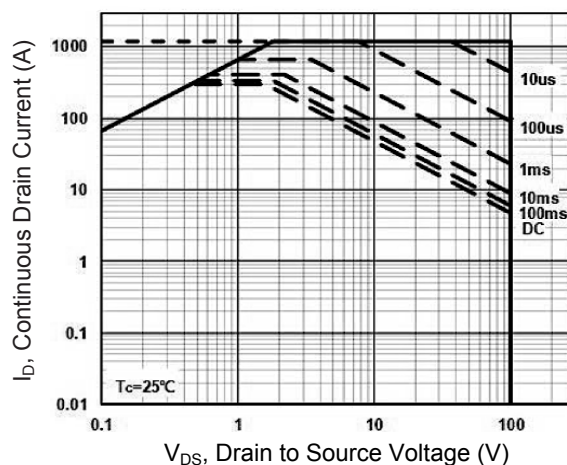
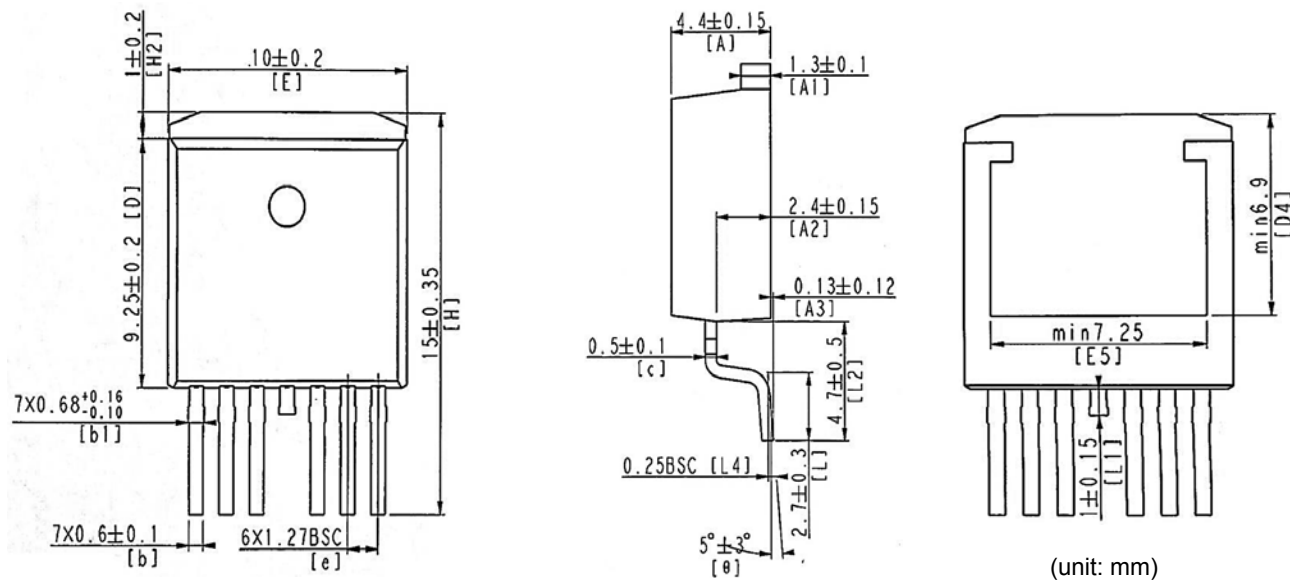


Figure 10. Maximum Safe Operation Area

Package Outline Dimensions (TO-263-7L)



Order Information

Device	Package	Marking	Carrier	Quantity
GSGT71R710	TO-263-7L	T71R710	Tape & Reel	800 Pcs / Reel